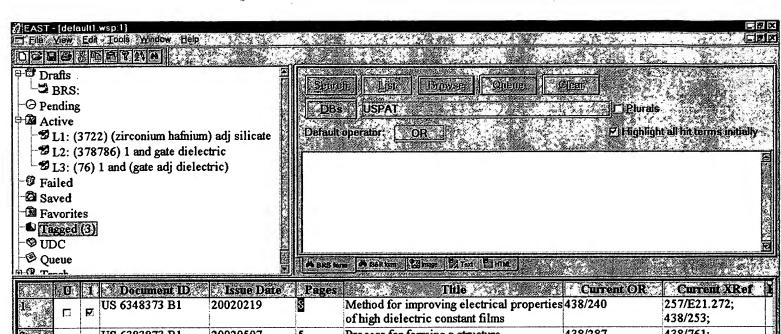


100	U,	1	Document ID	: Issué Date	Pages	Title	Current OR	Current XRef J
1		R	US 6399208 B	20030325	19	Chemical vapor deposition precursor composition for forming a metal silicate		
2	П	R	WO 200179578 A	20011025	29	New hexacoordinated silicon beta-diketonate compound is used for low		
3	Г	Þ	US 20020043666 A	20030416	14	Formation of insulation layer on semiconductor substrate comprises		
4	П	R	JP 11135774 A	19990521	46 🏑	HIGH-DIELECTRIC CONSTANT SILICATE GATE DIELECTRIC		
5	Г	F	US 6291283 B1	20010918	5	Method to form silicates as high dielectric constant materials		257/E21.274; 257/E21.625;
6	Г	R	US 6399208 B1	20020604	19	Source reagent composition and method for chemical vapor deposition formation	428/446	106/1.12; 106/1.22;
7	П	F	US 6544875 B1	20030408	6 L	Chemical vapor deposition of silicate high dielectric constant materials		438/216; 438/287;
8	Г	R	US 20010021589 A1	20010913	6 🗸	Method to form silicates as high dielectric constant materials		257/E21.193; 257/E21.274;
9	П	P	US 20020005556 A1	20020117	10	SILICATE GATE DIELECTRIC	257/381	257/382; 257/383;
10 ⊄	С	P	US 20030017715 A1	20030123	9_	Composite gate dielectric layer	,	438/787; 438/788;
117		Þ	US 20030139026 A1	20030724	10	Methods of forming binary noncrystalline oxide analogs of silicon dioxide		257/310; 438/585



10 A.	, O	1	Document ID	Issue Date 🕡	Pages	Title	Current OR	Current XRef
1	П	ᅜ	US 6348373 B1	20020219		Method for improving electrical properties of high dielectric constant films		257/E21.272; 438/253;
2	П	R	US 6383873 B1	20020507	5	Process for forming a structure		438/761; 438/762
3		R	US 6573160 B2	20030603	?	Method of recrystallizing an amorphous region of a semiconductor		438/198; 438/583